



# VOIDLESS HERMETICALLY SEALED SURFACE MOUNT STANDARD RECOVERY GLASS RECTIFIERS

Qualified to MIL-PRF-19500/420

## DESCRIPTION

This "standard recovery" surface mount rectifier diode series is military qualified and is ideal for high-reliability applications where a failure cannot be tolerated. These industry-recognized 5.0 amp rated rectifiers for working peak reverse voltages from 200 to 1000 volts are hermetically sealed with voidless-glass construction using an internal "*Category 1*" metallurgical bond. These devices are also available in axial-leaded packages for thru-hole mounting. Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time speeds.

Important: For the latest information, visit our website http://www.microsemi.com.

#### FEATURES

- Surface mount equivalent of JEDEC registered 1N5550 thru 1N5554 series.
- Voidless hermetically sealed glass package.
- Extremely robust construction.
- Quadruple-layer passivation.
- Internal "Category 1" metallurgical bonds.
- JAN, JANTX, JANTXV and JANS qualified versions available per MIL-PRF-19500/420.
- RoHS compliant versions available (commercial grade only).

#### **APPLICATIONS / BENEFITS**

- Standard recovery 5 amp 200 to 1000 volts rectifiers series.
- Military and other high-reliability applications.
- General rectifier applications including bridges, half-bridges, catch diodes, etc.
- High forward surge current capability.
- Low thermal resistance.
- Controlled avalanche with peak reverse power capability.
- Extremely robust construction.
- Inherently radiation hard as described in Microsemi "MicroNote 050".

#### **MAXIMUM RATINGS** @ $T_A = 25 \,^{\circ}C$ unless otherwise noted.

Parameters/Test Conditions		Symbol	Value	Unit
Junction and Storage Temperature		$T_J$ and $T_{STG}$	-65 to +175	°C
Thermal Resistance Junction-to-End Cap		R <sub>ØJEC</sub>	6.5	°C/W
Thermal Impedance @ 10 ms heating time (1)		Z <sub>ƏJX</sub>	1.5	°C/W
Maximum Forward Surge Current (8.3 ms half sine)		I <sub>FSM</sub>	100	Α
Average Rectified Forward Current <sup>(2)</sup>	@ T <sub>EC</sub> = 130 <sup>o</sup> C	I <sub>O(L)</sub>	5	А
Average Rectified Forward Current <sup>(3)</sup>	@ T <sub>A</sub> = 55 °C	I <sub>O2</sub> <sup>(2)</sup>	3	А
	@ T <sub>A</sub> = 100 °C	I <sub>O3</sub> <sup>(4)</sup>	2	Α
Working Peak Reverse Voltage	1N5550US	V <sub>RWM</sub>	200	V
	1N5551US		400	
	1N5552US		600	
	1N5553US		800	
	1N5554US		1000	
Solder Temperature @ 10 s		T <sub>SP</sub>	260	°C

See notes on next page.

<u>Qualified Levels</u>: JAN, JANTX, JANTXV and JANS



## "B" SQ-MELF (D-5B) Package

Also available in:

"B" Package (axial-leaded) 1N5550 – 1N5554

#### MSC – Lawrence

6 Lake Street, Lawrence, MA 01841 Tel: 1-800-446-1158 or (978) 620-2600 Fax: (978) 689-0803

#### MSC – Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

Website:

www.microsemi.com



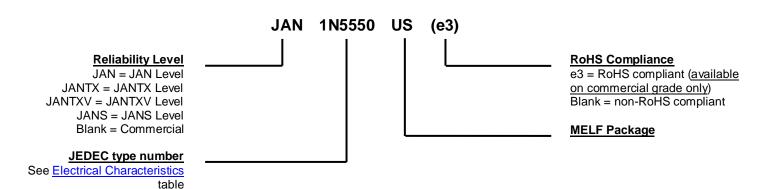
#### MAXIMUM RATINGS

- Notes: 1. Derate linearly at 66.6 mA/°C above T<sub>EC</sub> = 100 °C. An I<sub>O</sub> of up to 6 Amps is allowable provided that appropriate heat sinking or forced air cooling maintains the junction temperature at or below +200 °C.
  - 2. Derate linearly at 22.2 mA/°C from +55 °C to +100 °C.
  - 3. These I<sub>O</sub> ratings are for a thermally (PC boards or other) mounting methods where the lead or end-cap temperatures cannot be maintained and where thermal resistance from mounting point to ambient is still sufficiently controlled where T<sub>J(MAX)</sub> does not exceed 175 °C. This equates to R<sub>θJX</sub> ≤ 47 °C/W.
  - 4. Derate linearly at 26.7 mA/°C above  $T_{\text{A}}\text{=}+100~^{\circ}\text{C}$  to +175 °C ambient.

#### MECHANICAL and PACKAGING

- CASE: Hermetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: End caps are copper with tin/lead (Sn/Pb) finish. RoHS compliant matte-tin is available for commercial only.
- MARKING: Cathode band only.
- POLARITY: Cathode indicated by band.
- TAPE & REEL option: Standard per EIA-481-B. Consult factory for quantities.
- WEIGHT: 539 milligrams.
- See <u>Package Dimensions</u> and recommended <u>Pad Layout</u> on last page.

#### PART NOMENCLATURE



	SYMBOLS & DEFINITIONS		
Symbol	Definition		
V <sub>BR</sub>	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.		
V <sub>RWM</sub>	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range excluding all transient voltages (ref JESD282-B).		
Ι <sub>ο</sub>	Average Rectified Output Current: The Output Current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.		
VF	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.		
I <sub>R</sub>	Maximum Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.		
trr	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.		



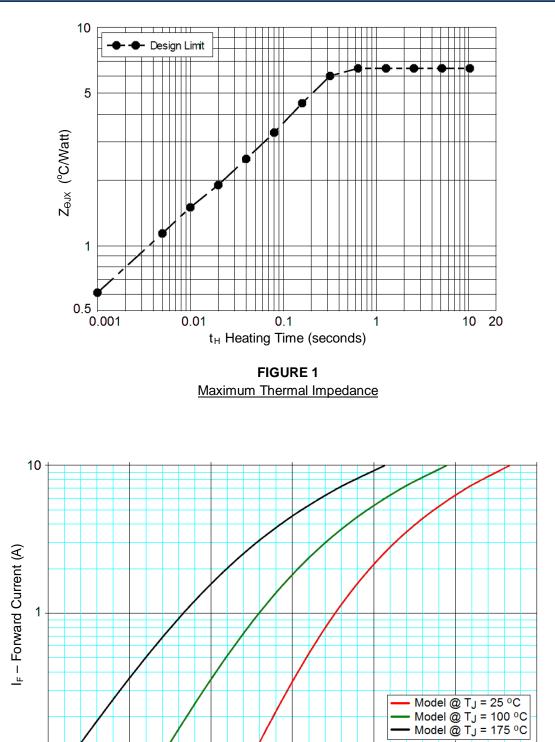
ТҮРЕ	MINIMUM BREAKDOWN VOLTAGE	FORWARD VOLTAGE V <sub>F</sub> @ 9 A (pk)		DOWN V <sub>F</sub> @ 9 A (pk) AGE		MAXIMUM REVERSE CURRENT I <sub>R</sub> @ V <sub>RWM</sub>	REVERSE RECOVERY trr
	V <sub>BR</sub> I <sub>R</sub> @ 50 μA Volts	MIN. Volts	MAX. Volts	μ <b>Α</b>	(Note 1) μs		
1N5550US	220	0.6 V (pk)	1.2 V (pk)	1.0	2.0		
1N5551US	440	0.6 V (pk)	1.2 V (pk)	1.0	2.0		
1N5552US	660	0.6 V (pk)	1.2 V (pk)	1.0	2.0		
1N5553US	880	0.6 V (pk)	1.3 V (pk)	1.0	2.0		
1N5554US	1100	0.6 V (pk)	1.3 V (pk)	1.0	2.0		

## **ELECTRICAL CHARACTERISTICS** @ $T_A = 25$ °C unless otherwise noted.

NOTE 1:  $I_F$  = 0.5 A,  $I_{RM}$  = 1.0 A,  $I_{R(REC)}$  = .250 A.



GRAPHS



0.1 0.50

0.60

0.70

0.80

V<sub>F</sub> - Forward Voltage (V)

FIGURE 4 Typical Forward Voltage vs. Forward Current

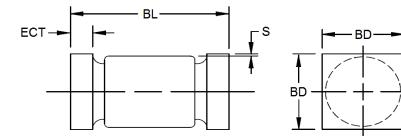
0.90

1.00

1.10



## PACKAGE DIMENSIONS

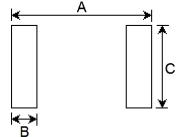


Ltr	Inch		Millimeters	
	MIN	MAX	MIN	MAX
BL	.200	.275	5.08	6.99
BD	.137	.186	3.48	4.72
ECT	.019	.034	0.48	0.86
S	.003		0.08	

#### NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Dimensions are pre-solder dip.
- 4. Minimum clearance of glass body to mounting surface on all orientations. 5. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi x$  symbology.
- 6. This package outline has also previously been identified as "D5B".

## PAD LAYOUT



Ltr	Inch	Millimeters	
Α	0.288	7.32	
В	0.070	1.78	
С	0.155	3.94	
<b>Note:</b> If mounting requires adhesive separate from the solder, an additional 0.080 inch diameter contact may be placed in the center between the pads as an optional spot for cement.			

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Authorized Distributor

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## Microchip:

JANTX1N5551US/TR JAN1N5553US/TR JANTXV1N5550US/TR JANS1N5550US/TR JANTX1N5554US/TR JAN1N5551US/TR JANTX1N5550US/TR JANTXV1N5551US/TR JANTXV1N5553US/TR JAN1N5554US/TR JANTX1N5553US/TR JANTX1N5552US/TR JANTXV1N5552US/TR 1N5550USe3 1N5550US/TR 1N5550USe3/TR 1N5551USe3 1N5551USe3/TR 1N5553US/TR 1N5551US/TR JANTXV1N5554US/TR JAN1N5550US/TR JAN1N5552US/TR JANTX1N5554US